

[METHOD OF FORMING LDD OF SEMI- CONDUCTOR DEVICES]

Abstract

A method of forming an LDD of a semiconductor device. A substrate having a polysilicon layer thereon is provided, wherein the polysilicon layer comprises a first region and a second region. A patterned photoresist layer is formed on the polysilicon layer for exposing the first region and covering the second region. The photoresist layer covering the second region comprises a middle portion and an edge portion, wherein the middle portion is thicker than the edge portion. Then, an ion implantation process is performed using the photoresist layer as a mask for forming a source/drain in the first region of the polysilicon layer and an LDD in the second region underneath the edge portion of the photoresist layer.